

Notice of References Cited

Application/Control No.

10/726,384

Applicant(s)/Patent Under
Reexamination
OOI ET AL.

Examiner

Savitri Mulpuri

Art Unit

2812

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	U	Yamad et al, "strained InGaAs/GaAs a single quntum well lasers with suitable absorbers fabricated by quntum well intermixing"Appl.Phys.Lett.60(20)18 May 1992, pp2463-2465
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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